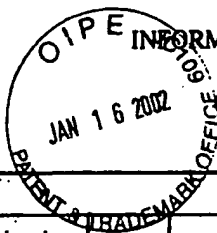


37 CFR 1.501

INFORMATION DISCLOSURE STATEMENT
IN A PATENT

(use several sheets if necessary)

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09/381,323Applicants
Thomas Aeugle, et al.Filing Date
09/16/1999Group Art Unit
2827

U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
TYT	AA	5,208,172	05-04-93	J. Fitch, et al.	—	—	—
TYT	AB	5,545,586	08-13-96	R. Koh	—	—	—
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	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
TYT	AL	EP 0 268 941	06-01-88	Europe	—	—	Abstract	X
TYT	AM	EP 0 430 514	06-05-91	Europe	—	—		X
TYT	AN	DE 196 21 244	11-14-96	Germany	—	—	Abstract	X
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TYT	AR	R. Loo, et al., "Vertical Si p-MOS transistor selectively grown by low pressure chemical vapour deposition", Thin Solid Films, Vol. 294, p. 267 (1997)						
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.